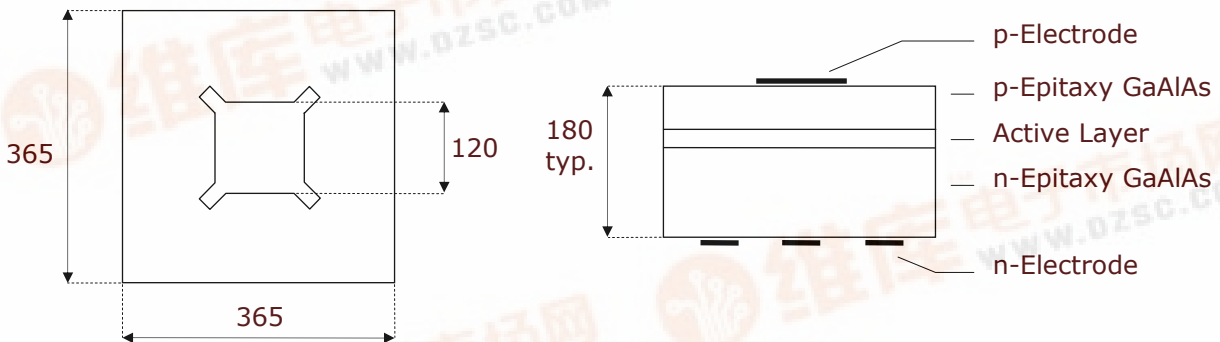


INFRA-RED **Item No.: 136274**

1. This specification applies to GaAlAs / GaAlAs Chips (substrate removed)
2. Structure
 - 2.1 Mesa structure
 - 2.2 Electrodes

p-side (anode)	Au alloy
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



Wire bond contact can also be square

4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	V_F	$I_F = 20 \text{ mA}$		1,35	1,60	V
Reverse voltage	V_R	$I_R = 10 \text{ }\mu\text{A}$	5			V
output Power *	Φ_e	$I_F = 20 \text{ mA}$	3,8	4,5		mW
$1/2 \lambda_p$		$I_F = 20 \text{ mA}$		42		nm
Switching time	t_r, t_f	$I_F = 20 \text{ mA}$		20		ns
Peak wavelength	λ	$I_F = 20 \text{ mA}$		850		nm

Power measurement at OSA on gold plate

5. Packing

- 1) wire bond side on top
- 2) back contact on top

6. Labeling

Type	Lot No.	Φ_e typ min max	Quantity
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